Electronic Supplementary Information

Rational bridging affording luminogen with AIE feature and high field effect mobility

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Contents

Fig. S5 Photographs of 4TPAE in toluene, THF, DCM and DMF taken under 365-nm UV light irridiation. Concentration = 5 μM.

Fig. S6 Photographs of the crystals of 4TPAE.

Fig. S7 OFET device structure based on 4TPAE.

Fig. S8 Power efficiency-voltage plots of the OLED devices of 4TPAE with a general configuration of ITO/X/TPBi/LiF/Al.

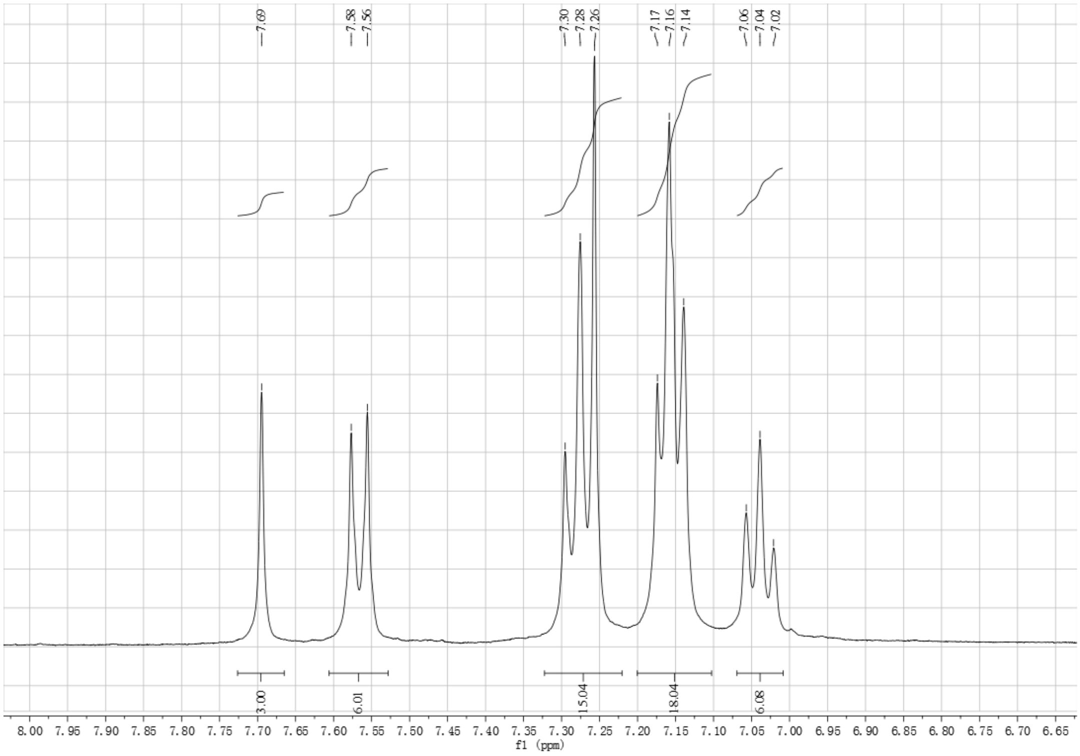


Fig. S1 ^{1}H NMR spectrum of 3TPAB in $CDCl_3$.

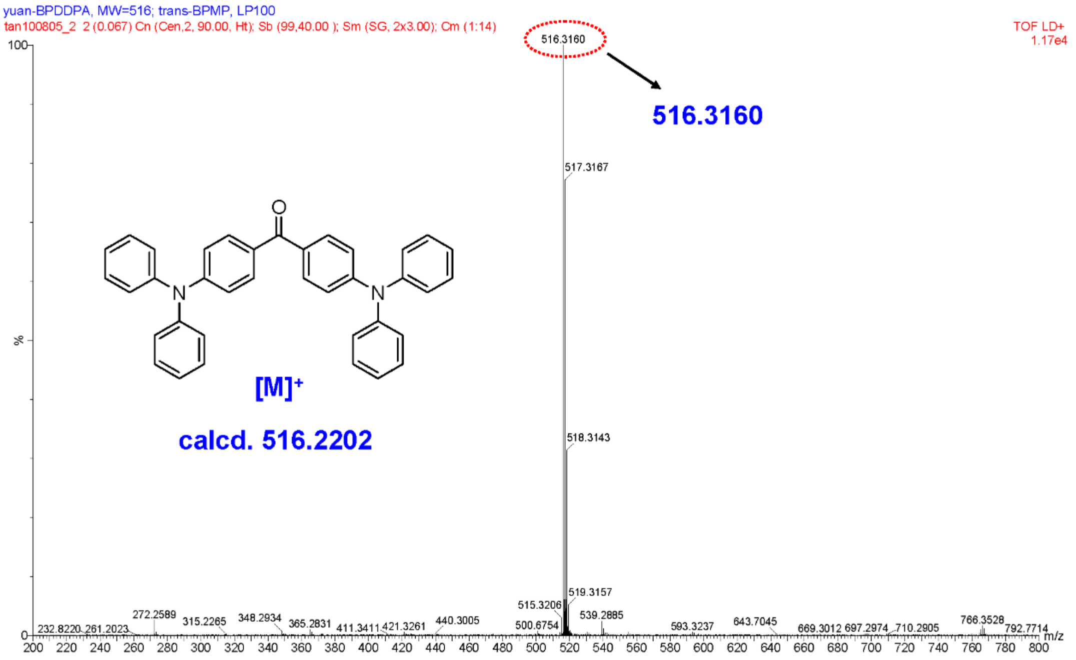


Fig. S2 HRMS of compound **5**.

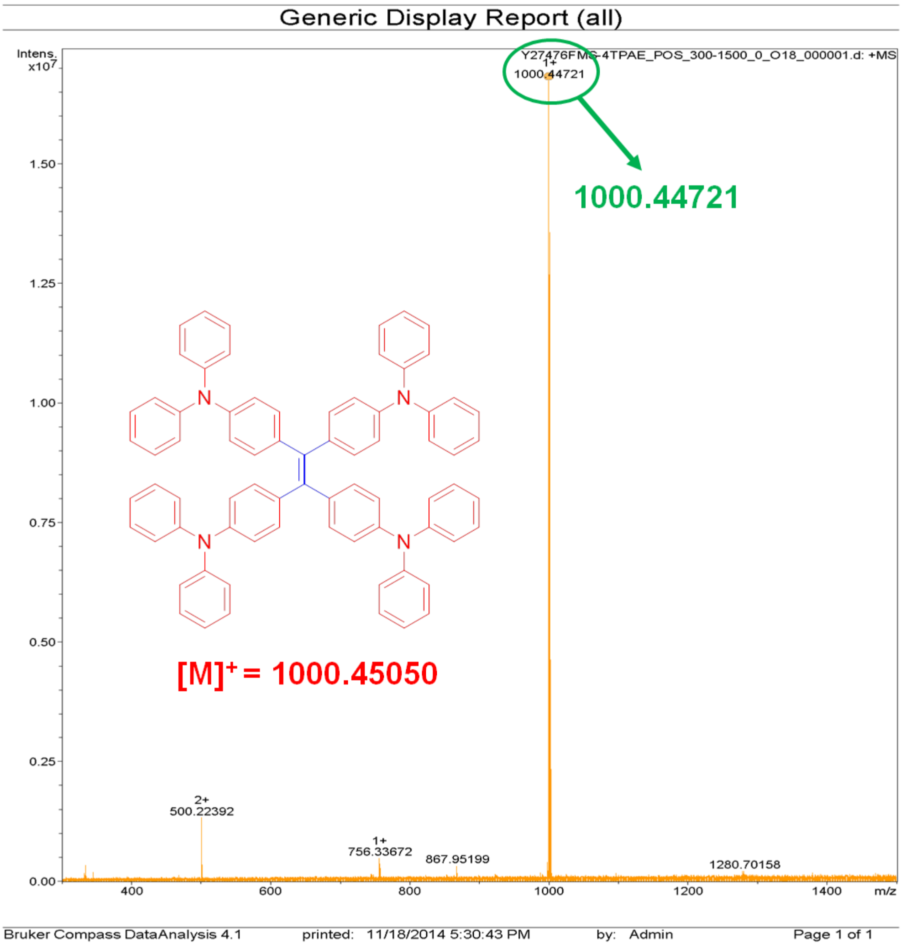


Fig. S3 HRMS of 4TPAE.

Table S1 Single crystal data of 4TPAE.

Compound reference	4TPAE
Chemical formula	$C_{74}H_{56}N_4$
Formula Mass	1001.23
Crystal system	
a/Å	10.6440(18)
b/ Å	14.262(4)
c/ Å	18.828(3)
α/ °	94.179(17)
β/ °	95.469(14)
γ/ °	108.415(19)
Unit cell volume/ $Å^3$	2683.4(9)
Temperature/K	173
Space group	P-1
No. of formula units per unit cell, Z	2
No. of reflections measured	13790
No. of independent reflections	8815
R_{int}	0.1467
Final R_1 values ($I > 2\sigma(I)$)	0.0606
Final $wR(F^2)$ values ($I > 2\sigma(I)$)	0.1111
Final R_1 values (all data)	0.2160
Final $wR(F^2)$ values (all data)	0.1574

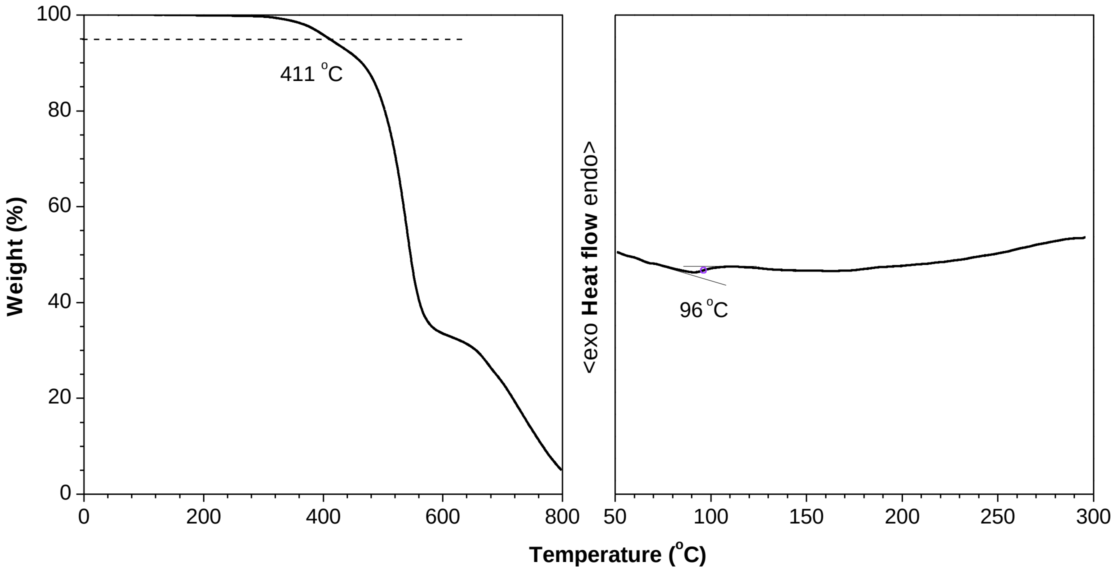
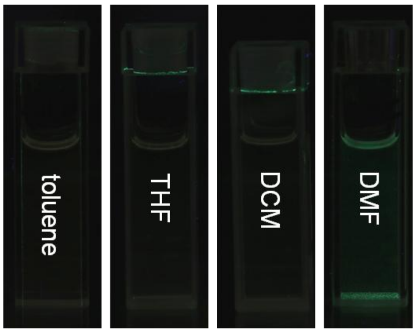


Fig. S4 (A) TGA and (B) DSC thermograms of 4TPAE recorded under nitrogen at a scan rate of 20 °C min^{-1}. The DSC curve was recorded during the first cooling cycle.



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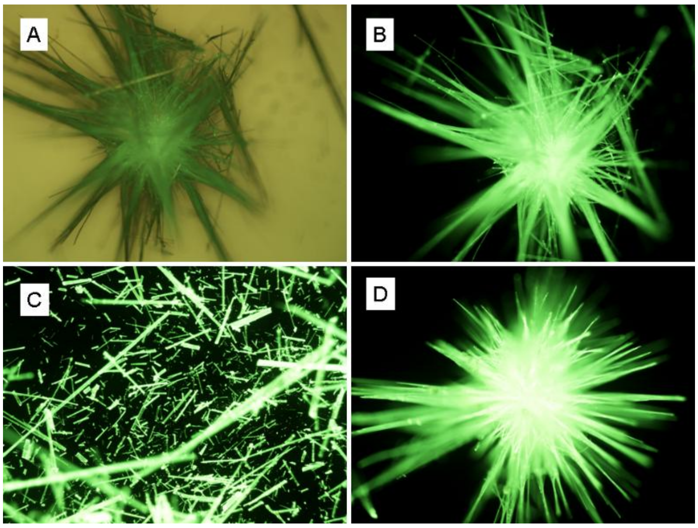

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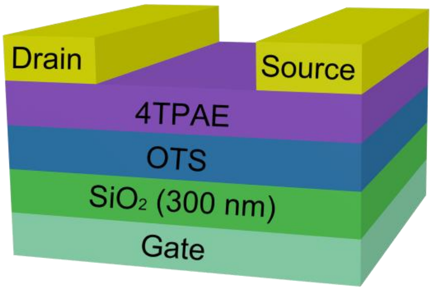

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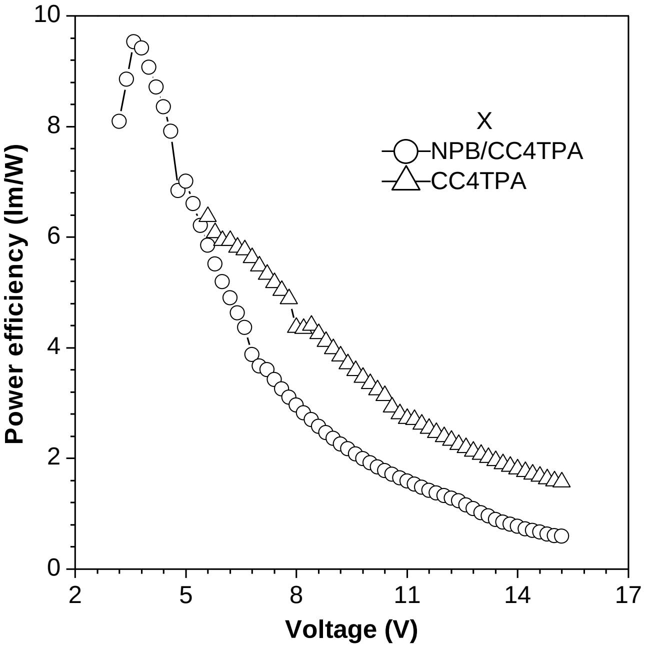

Fig. S8 Power efficiency-voltage plots of the OLED devices of 4TPAE with a general configuration of ITO/X/TPBi/LiF/Al.